# EH2900ETTTS-4.096M



#### EH29 00 ET T TS -4.096M

- Nominal Frequency 4.096MHz

Series -RoHS Compliant (Pb-free) 1.8V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability ±100ppm Maximum

Pin 1 Connection Tri-State (High Impedance)

Operating Temperature Range --40°C to +85°C

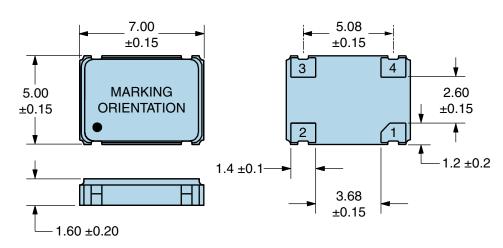
## Duty Cycle 50 ±5(%)

| Nominal Frequency                         | 4.096MHz   |  |
|---|--|--|
| Frequency Tolerance/Stability             | ±100ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, 260°C Reflow, Shock, and Vibration) |  |
| Aging at 25°C                             | ±5ppm/Year Maximum   |  |
| Operating Temperature Range               | -40°C to +85°C   |  |
| Supply Voltage                            | 1.8Vdc ±5%   |  |
| Input Current                             | 3.5mA Maximum (No Load)  |  |
| Output Voltage Logic High (Voh)           | 90% of Vdd Minimum (IOH = -8mA)  |  |
| Output Voltage Logic Low (Vol)            | 10% of Vdd Maximum (IOL = +8mA)  |  |
| Rise/Fall Time                            | 6nSec Maximum (Measured at 20% to 80% of waveform)   |  |
| Duty Cycle                                | 50 ±5(%) (Measured at 50% of waveform)   |  |
| Load Drive Capability                     | 15pF Maximum   |  |
| Output Logic Type                         | CMOS   |  |
| Pin 1 Connection                          | Tri-State (High Impedance)   |  |
| Tri-State Input Voltage (Vih and Vil)     | 90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)   |  |
| Standby Current                           | 10µA Maximum (Pin 1 = Ground)  |  |
| Absolute Clock Jitter                     | ±100pSec Maximum   |  |
| Start Up Time                             | 10mSec Maximum   |  |
| Storage Temperature Range                 | -55°C to +125°C  |  |
| ENVIRONMENTAL & MECHANICAL SPECIFICATIONS |  |  |
| ESD Susceptibility                        | MII -STD-883, Method 3015, Class 1, HBM: 1500V   |  |

| ESD Susceptibility           | MIL-STD-883, Method 3015, Class 1, HBM: 1500V |
|------------------------------|---|
| Fine Leak Test               | MIL-STD-883, Method 1014, Condition A         |
| Flammability                 | UL94-V0                                       |
| Gross Leak Test              | MIL-STD-883, Method 1014, Condition C         |
| Mechanical Shock             | MIL-STD-883, Method 2002, Condition B         |
| Moisture Resistance          | MIL-STD-883, Method 1004                      |
| Moisture Sensitivity         | J-STD-020, MSL 1                              |
| Resistance to Soldering Heat | MIL-STD-202, Method 210, Condition K          |
| Resistance to Solvents       | MIL-STD-202, Method 215                       |
| Solderability                | MIL-STD-883, Method 2003                      |
| Temperature Cycling          | MIL-STD-883, Method 1010, Condition B         |
| Vibration                    | MIL-STD-883, Method 2007, Condition A         |

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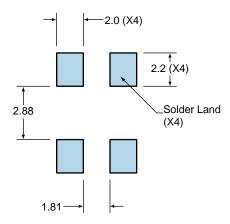
### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**



| PIN  | CONNECTION   |
|------|--|
| 1    | Tri-State  |
| 2    | Case Ground  |
| 3    | Output   |
| 4    | Supply Voltage                                       |
| LINE | MARKING  |
| 1    | ECLIPTEK   |
| 2    | 4.096M   |
| 3    | XXXXXX<br>XXXXX=Ecliptek<br>Manufacturing Identifier |

#### Suggested Solder Pad Layout

All Dimensions in Millimeters

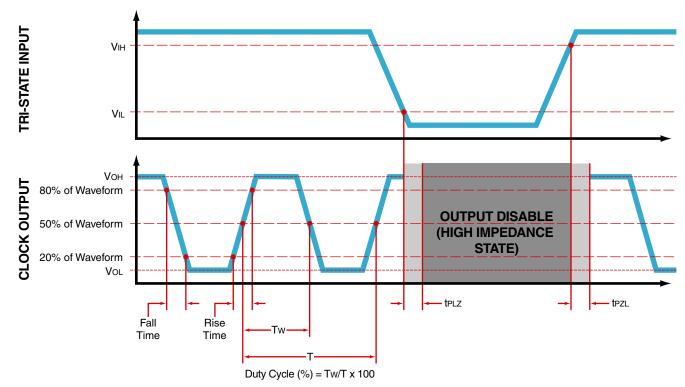


All Tolerances are ±0.1

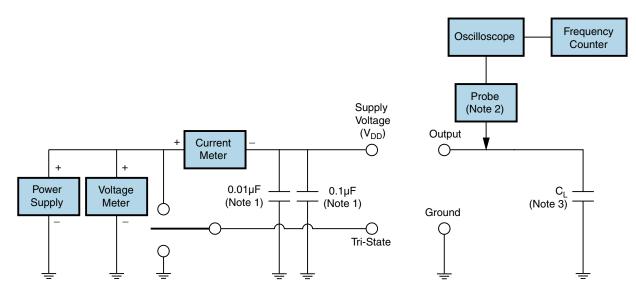
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#### **OUTPUT WAVEFORM & TIMING DIAGRAM**



**Test Circuit for CMOS Output** 



- Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.



## **Recommended Solder Reflow Methods**

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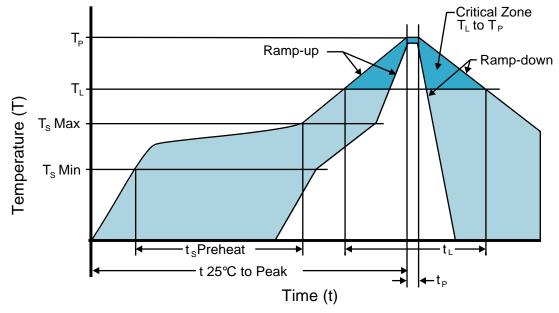
### **High Temperature Infrared/Convection**

| $T_s$ MAX to $T_L$ (Ramp-up Rate)                           | 3°C/second Maximum                                |
|---|---|
| Preheat   |   |
| - Temperature Minimum (T <sub>s</sub> MIN)                  | 150°C   |
| - Temperature Typical (T <sub>s</sub> TYP)                  | 175°C   |
| <ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul> | 200°C   |
| - Time (t <sub>s</sub> MIN)                                 | 60 - 180 Seconds                                  |
| Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )            | 3°C/second Maximum                                |
| Time Maintained Above:                                      |   |
| - Temperature (T∟)  | 217°C   |
| - Time (t∟)   | 60 - 150 Seconds                                  |
| Peak Temperature (T <sub>P</sub> )                          | 260°C Maximum for 10 Seconds Maximum              |
| Target Peak Temperature (T <sub>P</sub> Target)             | 250°C +0/-5°C                                     |
| Time within 5°C of actual peak (t <sub>p</sub> )            | 20 - 40 seconds                                   |
| Ramp-down Rate  | 6°C/second Maximum                                |
| Time 25°C to Peak Temperature (t)                           | 8 minutes Maximum                                 |
| Moisture Sensitivity Level                                  | Level 1   |
| Additional Notes  | Temperatures shown are applied to body of device. |



## **Recommended Solder Reflow Methods**

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### Low Temperature Infrared/Convection 240°C

| $T_s$ MAX to $T_L$ (Ramp-up Rate)                | 5°C/second Maximum                                     |
|--|--|
| Preheat  |  |
| - Temperature Minimum (T <sub>s</sub> MIN)       | N/A  |
| - Temperature Typical (T <sub>s</sub> TYP)       | 150°C  |
| - Temperature Maximum (T <sub>s</sub> MAX)       | N/A  |
| - Time (t <sub>s</sub> MIN)                      | 60 - 120 Seconds                                       |
| Ramp-up Rate (T⊾ to T <sub>P</sub> )             | 5°C/second Maximum                                     |
| Time Maintained Above:                           |  |
| - Temperature (T∟)                               | 150°C  |
| - Time (t∟)                                      | 200 Seconds Maximum                                    |
| Peak Temperature (T <sub>P</sub> )               | 240°C Maximum  |
| Target Peak Temperature (T <sub>P</sub> Target)  | 240°C Maximum 1 Time / 230°C Maximum 2 Times           |
| Time within 5°C of actual peak (t <sub>p</sub> ) | 10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time |
| Ramp-down Rate                                   | 5°C/second Maximum                                     |
| Time 25°C to Peak Temperature (t)                | N/A  |
| Moisture Sensitivity Level                       | Level 1  |
| Additional Notes                                 | Temperatures shown are applied to body of device.      |

#### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)